

NGTB25N120LWG

IGBT 1200V 25A FS1 Gen Mkt

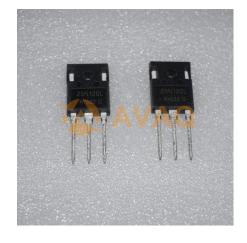
Manufacturer: ON Semiconductor, LLC

Package/Case: TO-247

Product Type: Thyristors

RoHS Compliant/Lead free RoHS RoHS:

Lifecycle: Obsolete



Images are for reference only

General Description

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop (FS) Trench construction, and provides superior performance in demanding switching applications, offering both low on-state voltage and minimal switching loss. The IGBT is well suited for resonant or soft switching applications. Incorporated into the device is a rugged co-packaged free wheeling diode with a low forward voltage.

Key Features Application

Low Saturation Voltage using Trench with Fieldstop Technology

Low Switching Loss

Industrial Switching





Recommended For You

NGTB40N120FL3WG

ON Semiconductor, LLC

TO-247

NGB8202NT4

ON Semiconductor, LLC

TO-263

NGTB40N120FL2WG

ON Semiconductor, LLC

TO-247

NGTB50N120FL2WG

ON Semiconductor, LLC

TO-247

NGTB25N120FL3WG

ON Semiconductor, LLC

TO-247-3

NGIB50N60FLWG

ON Semiconductor, LLC

TO-247

NGTB75N65FL2WG

ON Semiconductor, LLC

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NGTB40N120L3WG

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NGTB35N65FL2WG

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NGTB15N120IHLWG

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NGTB40N60IHLWG

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NGTB15N120FL2WG

ON Semiconductor, LLC

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NGTB05N60R2DT4G

ON Semiconductor, LLC

TO252

NGTB30N135IHRWG

ON Semiconductor, LLC

TO-247